

Abstracts

15-Watt Internally Matched GaAs FETs and 20-Watt Amplifier Operating at 6 GHz

K. Honjo, Y. Takayama, T. Furutsuka, A. Higashisaka and F. Hasegawa. "15-Watt Internally Matched GaAs FETs and 20-Watt Amplifier Operating at 6 GHz." 1979 MTT-S International Microwave Symposium Digest 79.1 (1979 [MWSYM]): 289-291.

6-GHz 15-Watt and 8-GHz 10-Watt internally matched GaAs FETs have been developed. The lumped-element two section input matching network is formed on ceramic plates with a high dielectric constant. The distributed single section output circuit is formed in microstrip pattern on an alumina plate. A 6-GHz 20-Watt balanced amplifier module has been realized using the internally matched devices which operate without any external matching.

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